NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRA1014-35** is Designed for Class C, Common Base Wideband Large Signal Amplifier Applications From 1.0 GHz to 1.4 GHz.

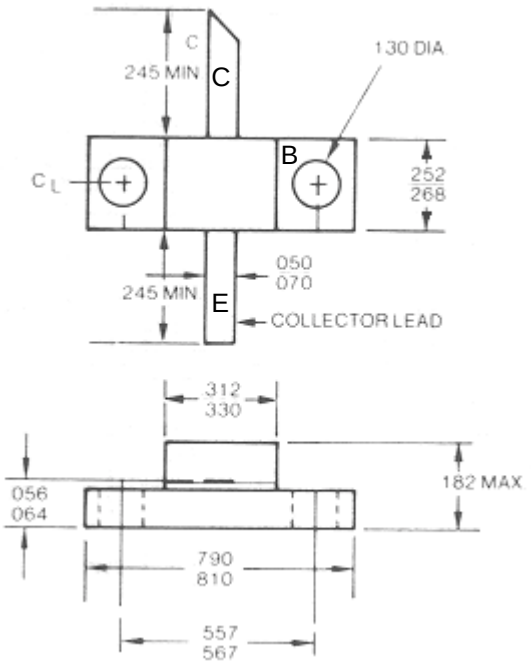
FEATURES:

- Diffused Ballast Resistors.
- Internal Matching Network
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	5.0 A (CONT)
V_{CES}	50 V
V_{EBO}	3.5 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .320 SQ 2L FLG



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 200 mA	50			V
BV_{EBO}	I_E = 2.5 mA	3.5			V
I_{CBO}	V_{CB} = 28 V			5.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	10		100	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			24	pF
G_{PB} η_C	V_{CE} = 28 V P_{out} = 35 W f = 1.0 GHz & 1.4 GHz	7.0 50			dB %

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Specifications are subject to change without notice.